



MSRT20060(A) thru MSRT200100(A)

Silicon Standard Recovery Diode

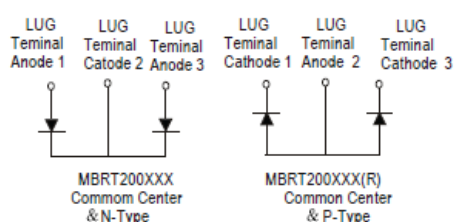
$V_{RRM} = 600 \text{ V} - 1600 \text{ V}$

$I_F = 200 \text{ A}$

Features

- High Surge Capability
- Types up to 1600 V V_{RRM}

Three Tower Package



Maximum ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	MSRT20060(A)	MSRT20080(A)	MSRT200100(A)	Unit
Repetitive peak reverse voltage	V_{RRM}		600	800	1000	V
RMS reverse voltage	V_{RMS}		424	566	707	V
DC blocking voltage	V_{DC}		600	800	1000	V
Continuous forward current	I_F	$T_C \leq 140^\circ\text{C}$	200	200	200	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25^\circ\text{C}$, $t_p = 8.3 \text{ ms}$	3000	3000	3000	A
Operating temperature	T_j		-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	MSRT20060(A)	MSRT20080(A)	MSRT200100(A)	Unit
Diode forward voltage	V_F	$I_F = 200 \text{ A}$, $T_j = 25^\circ\text{C}$	1.2	1.2	1.2	V
Reverse current	I_R	$V_R = 600 \text{ V}$, $T_j = 25^\circ\text{C}$	10	10	10	μA
		$V_R = 600 \text{ V}$, $T_j = 150^\circ\text{C}$	5	5	5	mA

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		0.18	0.18	0.18	$^\circ\text{C/W}$
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Figure .1- Typical Forward Characteristics

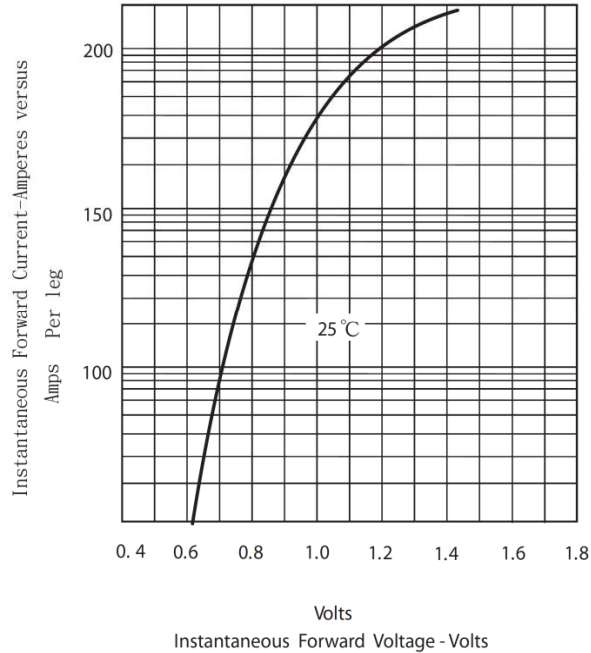


Figure.2 Forward Derating Curve

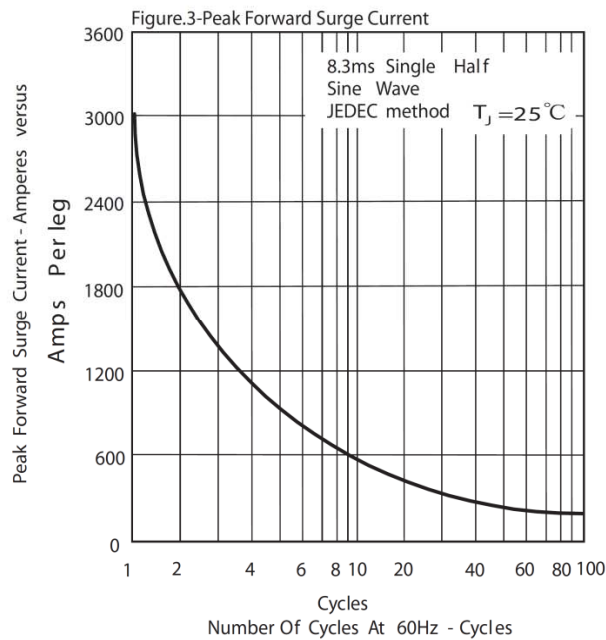
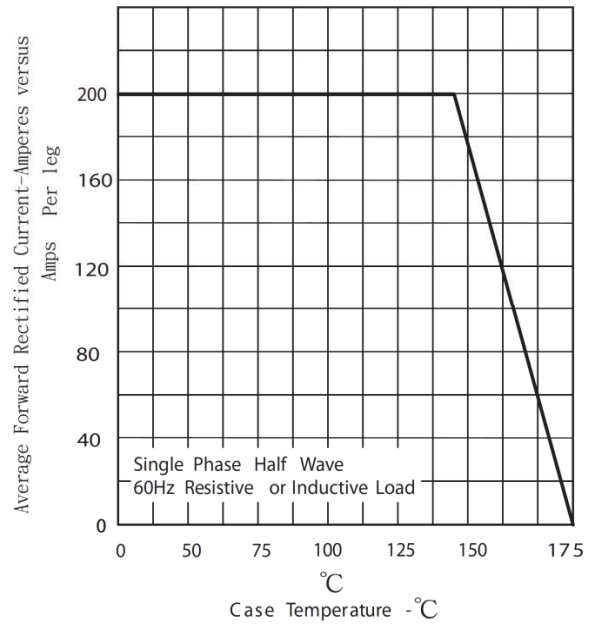


Figure .4 -Typical Reverse Characteristics

